

WHAT IS CLAIMED IS:

1. A semiconductor integrated circuit device comprising:

a logic circuit including a plurality of areas,
each of the areas including at least a first MOS
transistor of a first conductivity type;

first and second power supply lines to supply the
logic circuit with a supply voltage;

first substrate bias voltage supply line;

a substrate bias control circuit including a
plurality of second MOS transistors of the first
conductivity type, at least one of the second MOS
transistor being provided to each of the areas;

wherein a source of the first MOS transistor is
coupled to the first power supply line, a drain of the
first MOS transistor is coupled to the second power
supply line and a body of the first MOS transistor is
coupled to the first substrate bias voltage supply line;

wherein a source-drain path of each of the second
MOS transistor is coupled between the first power
supply line and the first substrate bias voltage line;
and

wherein when the supply voltage is activated, the
plurality of the second MOS transistors are controlled
to be ON state.